

<b>SPEC SHEET (FOR REFERENCE)</b>	SHEET No.	<b>G05041A</b>	Page.
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TYPE : 6PT2002N1T\*\*

CHIP SIZE	0.23 * 0.23 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	290,000 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	20	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	0.2	A

\* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±1	uA	VGS=±8.0V VDS=0V
2	IDSS			500	nA	VDS=20V VGS=0V
3	BVDSS	22			V	ID=100uA
4	VTH	0.5		1.0	V	ID=250uA
5	Ron 1		1.7	3.0	Ω	ID=100mA VGS=4.5V
6	Ron 2		3.5	6.0	Ω	ID=20mA VGS=1.8V
7	VSD			1.0	V	IS=10mA

※ Built-in ZD between Gate and Source. ESD Protected (350V)

TENTATIVE

NOTE: